

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Toshiyuki NAKAYAMA

Application No.: 09/582,351

Filed: August 11, 2000

For: SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURE  
THEREOF, CIRCUIT BOARD AND ELECTRONIC INSTRUMENT



Group Art Unit: 2815

Examiner: C. Chu

Docket No.: 106386

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T. Flower

AMENDMENT UNDER 37 C.F.R. §1.111

Director of the U.S. Patent and Trademark Office  
Washington, D.C. 20231

Sir:

In reply to the Office Action dated May 23, 2001, please amend the above-identified application as follows:

IN THE SPECIFICATION:

Page 12, lines 3-18, delete current paragraph and insert therefor:

On the surface of the base material of the substrate 10, the film 14 is formed. The film 14 preferably has lower adhesion with the adhesive 30 than with the surface of the base material of the substrate 10. The film 14 is formed to avoid at least one or all of the leads 12. The film 14 is formed so as not to contact at least one or all of the leads 12. Of the plurality of leads 12, not all but at least one may contact the film 14. For example, by contacting leads 12 to be connected to ground potential (GND potential) with the film 14 so as to be electrically conductive, the whole of the film 14 may be at ground potential (GND potential). In this case, since the film 14 which is larger than the leads 12 is at ground potential (GND

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